



## Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

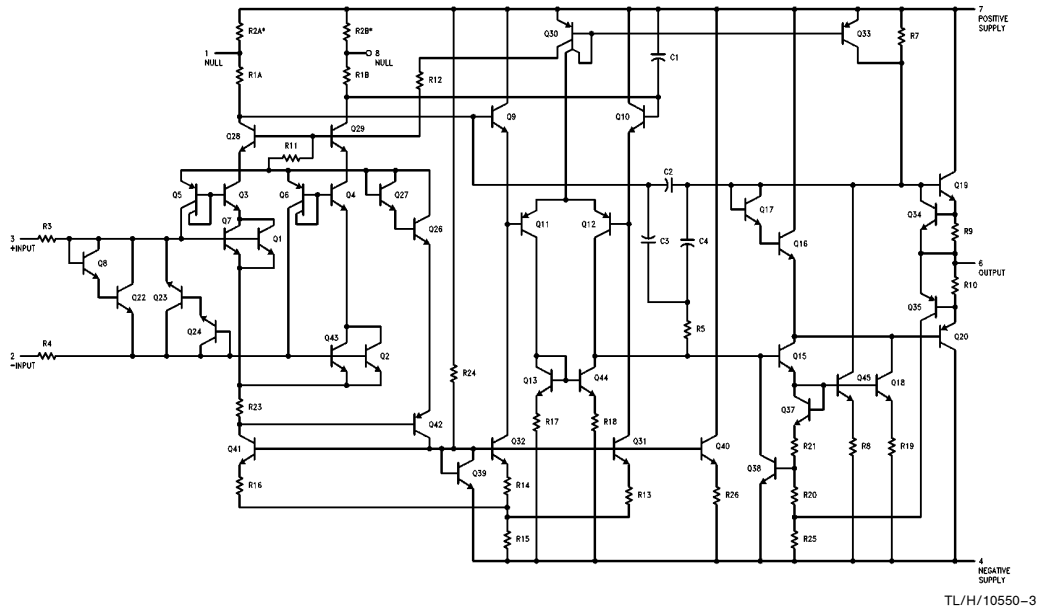
Supply Voltage	$\pm 22\text{V}$
Internal Power Dissipation (Note 5)	500 mW
Differential Input Voltage	$\pm 30\text{V}$
Input Voltage (Note 6)	$\pm 22\text{V}$
Output Short-Circuit Duration	Continuous

Storage Temperature Range	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Lead Temperature (Soldering, 60 sec.)	$260^{\circ}\text{C}$
Junction Temperature	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$

## Operating Temperature Range

OP-07E, OP-07C, OP-07D	$0^{\circ}\text{C}$ to $+70^{\circ}\text{C}$
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## Simplified Schematic



\*R2A and R2B are electronically trimmed on chip at the factory for minimum offset voltage.

## Electrical Characteristics

Unless otherwise specified,  $V_S = \pm 15V$ ,  $T_A = 25^\circ C$ . **Boldface** type refers to limits over  $0^\circ C \leq T_A \leq 70^\circ C$

Symbol	Parameter	Conditions	OP-07E			OP-07C			Units
			Min	Typ	Max	Min	Typ	Max	
$V_{OS}$	Input Offset Voltage	(Note 1)		30 <b>45</b>	75 <b>130</b>		60 <b>85</b>	150 <b>250</b>	$\mu V$
$V_{OS/t}$	Long-Term $V_{OS}$ Stability	(Note 2)		0.3	1.5		0.4	2.0	$\mu V/Mo$
$I_{OS}$	Input Offset Current			0.5 <b>0.9</b>	3.8 <b>5.3</b>		0.8 <b>1.6</b>	6.0 <b>8.0</b>	nA
$I_B$	Input Bias Current			$\pm 1.2$ $\pm$ <b>1.5</b>	$\pm 4.0$ $\pm$ <b>5.5</b>		$\pm 1.8$ $\pm$ <b>2.2</b>	$\pm 7.0$ $\pm$ <b>9.0</b>	nA
$e_{np-p}$	Input Noise Voltage	0.1 Hz to 10 Hz (Note 3)		0.35	0.6		0.38	0.65	$\mu V_{p-p}$
$e_n$	Input Noise Voltage Density	$f_O = 10$ Hz $f_O = 100$ Hz (Note 3) $f_O = 1000$ Hz		10.3 10.0 9.6	18.0 13.0 11.0		10.5 10.2 9.8	20.0 13.5 11.5	$nV/\sqrt{Hz}$
$i_{np-p}$	Input Noise Current	0.1 Hz to 10 Hz (Note 3)		14	30		15	35	$pA_{p-p}$
$i_n$	Input Noise Current Density	$f_O = 10$ Hz $f_O = 100$ Hz (Note 3) $f_O = 1000$ Hz		0.32 0.14 0.12	0.80 0.23 0.17		0.35 0.15 0.13	0.90 0.27 0.18	$pA/\sqrt{Hz}$
$R_{IN}$	Input Resistance Differential-Mode	(Note 4)	15	50		8	33		$M\Omega$
$R_{INCM}$	Input Resistance Common-Mode			160			120		$G\Omega$
IVR	Input Voltage Range		$\pm 13.0$	$\pm 14.0$		$\pm 13$	$\pm 14$		V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 13V$	106 <b>103</b>	123 <b>123</b>		100 <b>97</b>	120 <b>120</b>		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 3V$ to $\pm 18V$ $V_S = \pm 3V$ to $\pm 18V$		5 <b>7</b>	20 <b>32</b>		7 <b>10</b>	32 <b>51</b>	$\mu V/V$
$A_{VO}$	Large Signal Voltage Gain	$R_L \geq 2 k\Omega$ , $V_O = \pm 10V$ $R_L \geq 2 k\Omega$ $R_L \geq 500\Omega$ , $V_O = \pm 0.5V$ , $V_S = \pm 3V$ (Note 4)	200 <b>180</b> 150	500 <b>450</b> 400		120 <b>100</b> 100	400 <b>400</b> 400		V/mV
$V_O$	Output Voltage Swing	$R_L \geq 10 k\Omega$ $R_L \geq 2 k\Omega$ $R_L \geq 2 k\Omega$ $R_L \geq 1 k\Omega$	$\pm 12.5$ $\pm 12.0$ $\pm$ <b>12.0</b> $\pm 10.5$	$\pm 13.0$ $\pm 12.8$ $\pm$ <b>12.6</b> $\pm 12.0$		$\pm 12.0$ $\pm 11.5$ $\pm$ <b>11.0</b>	$\pm 13.0$ $\pm 12.8$ $\pm$ <b>12.6</b> $\pm 12.0$		V
SR	Slew Rate	$R_L \geq 2 k\Omega$ (Note 3)	0.1	0.3		0.1	0.3		$V/\mu s$
BW	Closed-Loop Bandwidth	$A_{VCL} = +1$ (Note 3)	0.4	0.6		0.4	0.6		MHz
$R_O$	Output Resistance	$V_O = 0$ , $I_O = 0$		60			60		$\Omega$
$P_d$	Power Consumption	$V_S = \pm 15V$ , No Load $V_S = \pm 3V$ , No Load		75 4	120 6		80 4	150 8	mW
	Offset Adj. Range	$R_P = 20 k\Omega$		$\pm 4$			$\pm 4$		mV
TCV <sub>OS</sub>	Average Input Offset Voltage Drift Without External Trim	(Note 4)		<b>0.3</b>	<b>1.3</b>		<b>0.5</b>	<b>1.8</b>	$\mu V/^\circ C$
TCV <sub>OSn</sub>	With External Trim	$R_P = 20 k\Omega$ (Note 4)		<b>0.3</b>	<b>1.3</b>		<b>0.4</b>	<b>1.6</b>	
TCI <sub>OS</sub>	Average Input Offset Current Drift	(Note 3)		<b>8</b>	<b>35</b>		<b>12</b>	<b>50</b>	$pA/^\circ C$
TCI <sub>B</sub>	Average Input Bias Current Drift	(Note 3)		<b>13</b>	<b>35</b>		<b>18</b>	<b>50</b>	$pA/^\circ C$

## Electrical Characteristics

Unless otherwise specified,  $V_S = \pm 15V$ ,  $T_A = 25^\circ C$ . **Boldface** type refers to limits over  $0^\circ C \leq T_A \leq +70^\circ C$

Symbol	Parameter	Conditions	OP-07D			Units
			Min	Typ	Max	
$V_{OS}$	Input Offset Voltage	(Note 1)		60 <b>85</b>	150 <b>250</b>	$\mu V$
$V_{OS}/t$	Long-Term $V_{OS}$ Stability	(Note 2)		0.5	3.0	$\mu V/Mo$
$I_{OS}$	Input Offset Current			0.8 <b>1.6</b>	6.0 <b>8.0</b>	nA
$I_B$	Input Bias Current			$\pm 2.0$ $\pm$ <b>3.0</b>	$\pm 12.0$ $\pm$ <b>14.0</b>	nA
$e_{np-p}$	Input Noise Voltage	0.1 Hz to 10 Hz (Note 3)		0.38	0.65	$\mu Vp-p$
$e_n$	Input Noise Voltage Density	$f_O = 10$ Hz $f_O = 100$ Hz (Note 3) $f_O = 1000$ Hz		10.5 10.3 9.8	20.0 13.5 11.5	$nV/\sqrt{Hz}$
$i_{np-p}$	Input Noise Current	0.1 Hz to 10 Hz (Note 3)		15	35	$pAp-p$
$i_n$	Input Noise Current Density	$f_O = 10$ Hz $f_O = 100$ Hz (Note 3) $f_O = 1000$ Hz		0.35 0.15 0.13	0.90 0.27 0.18	$pA/\sqrt{Hz}$
$R_{IN}$	Input Resistance Differential-Mode	(Note 4)	7	31		$M\Omega$
$R_{INCM}$	Input Resistance Common-Mode			120		$G\Omega$
IVR	Input Voltage Range		$\pm 13$	$\pm 14$		V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 13V$	94 <b>94</b>	110 <b>106</b>		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 3V$ to $\pm 18V$		7 <b>10</b>	32 <b>51</b>	$\mu V/V$
$A_{VO}$	Large Signal Voltage Gain	$R_L \leq 2 k\Omega$ , $V_O = \pm 10V$ $R_L = 2 k\Omega$ , $V_O = \pm 10V$ $R_L \geq 500\Omega$ , $V_O = \pm 0.5V$ , $V_S \pm 3V$ (Note 4)	120 <b>100</b>	400 <b>400</b> 400		V/mV
$V_O$	Output Voltage Swing	$R_L \geq 10 k\Omega$ $R_L \geq 2 k\Omega$ $R_L \geq 2 k\Omega$ $R_L \geq 1 k\Omega$	$\pm 12.0$ $\pm 11.5$ $\pm$ <b>11.0</b>	$\pm 13.0$ $\pm 12.8$ $\pm$ <b>12.6</b> $\pm 12.0$		V
SR	Slew Rate	$R_L \geq 2 k\Omega$ (Note 3)	0.1	0.3		$V/\mu s$
BW	Closed-Loop Bandwidth	$A_{VCL} = +1$ (Note 3)	0.4	0.6		MHz
RO	Output Resistance	$V_O = 0$ , $I_O = 0$		60		$\Omega$
$P_d$	Power Consumption	$V_S = \pm 15V$ , No Load $V_S = \pm 3V$ , No Load		80 4	150 8	mW
	Offset Adj. Range	$R_P = 20 k\Omega$		$\pm 4$		mV
$TCV_{OS}$	Average Input Offset Voltage Drift Without External Trim	(Note 4)		<b>0.7</b>	<b>2.5</b>	$\mu V/^\circ C$
$TCV_{OSn}$	With External Trim	$R_P = 20 k\Omega$ (Note 4)		<b>0.7</b>	<b>2.5</b>	$\mu V/^\circ C$
$TCI_{OS}$	Average Input Offset Current Drift	(Note 3)		<b>12</b>	<b>50</b>	$pA/^\circ C$
$TCI_B$	Average Input Bias Current Drift	(Note 3)		<b>18</b>	<b>50</b>	$pA/^\circ C$

**Note 1:**  $V_{OS}$  is measured approximately 0.5 second after application of power.

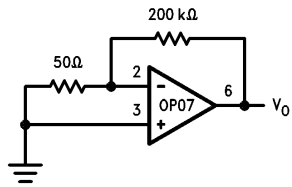
**Note 2:** Long-Term Offset Voltage Stability refers to the averaged trend line of  $V_{OS}$  vs Time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in  $V_{OS}$  during the first 30 operating days are typically  $2.5 \mu V$ . Parameter is sample tested.

**Note 3:** Sample Tested.

**Note 4:** Guaranteed by design.

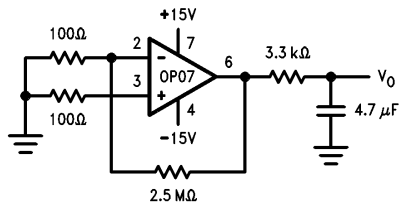
## Test Circuits

Offset Voltage Test Circuit



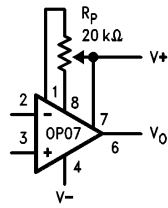
TL/H/10550-4

Low Frequency Noise Test Circuit

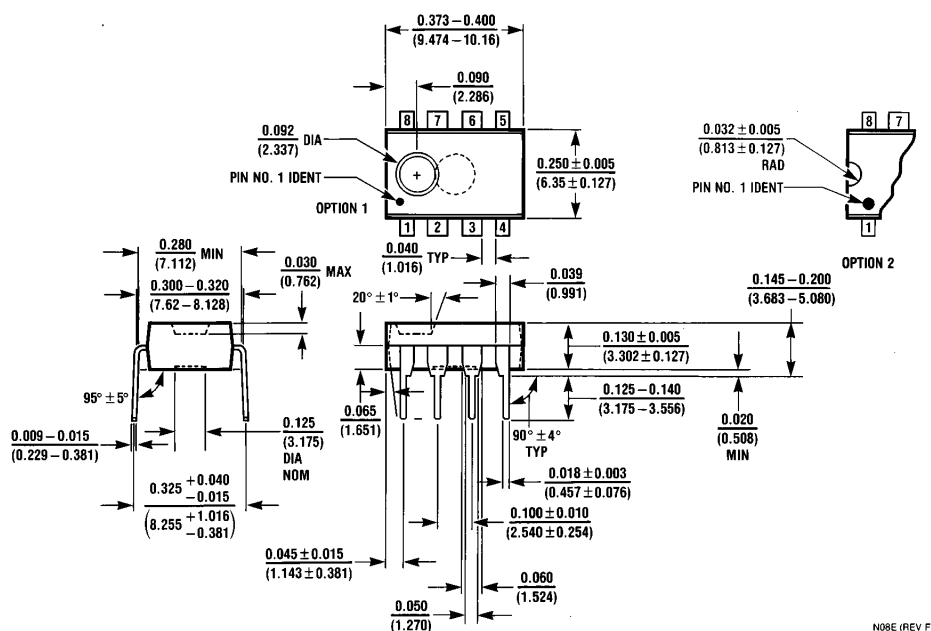


TL/H/10550-5

Optional Offset Nulling Circuit



TL/H/10550-6

**Physical Dimensions** inches (millimeters) (Continued)

**Order Number OP-07EP, OP-07CP or OP-07DP**  
**NS Package Number N08E**

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